

MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

Monolithic Dual Switching Diodes

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage MMBD2835LT1G, SMMBD2835LT1G MMBD2836LT1G	V_R	35 75	Vdc
Forward Current	I_F	100	mAdc

THERMAL CHARACTERISTICS

Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

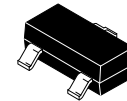
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

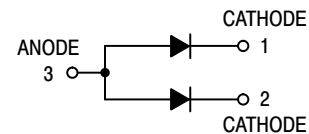


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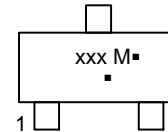
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SOT-23 (TO-236AB)
CASE 318-08
STYLE 12



MARKING DIAGRAM



xxx = Specific Device Code
A3X = MMBD2835LT1G
SMMBD2835LT1G
A2X = MMBD2836LT1G
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBD2835LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBD2835LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD2836LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

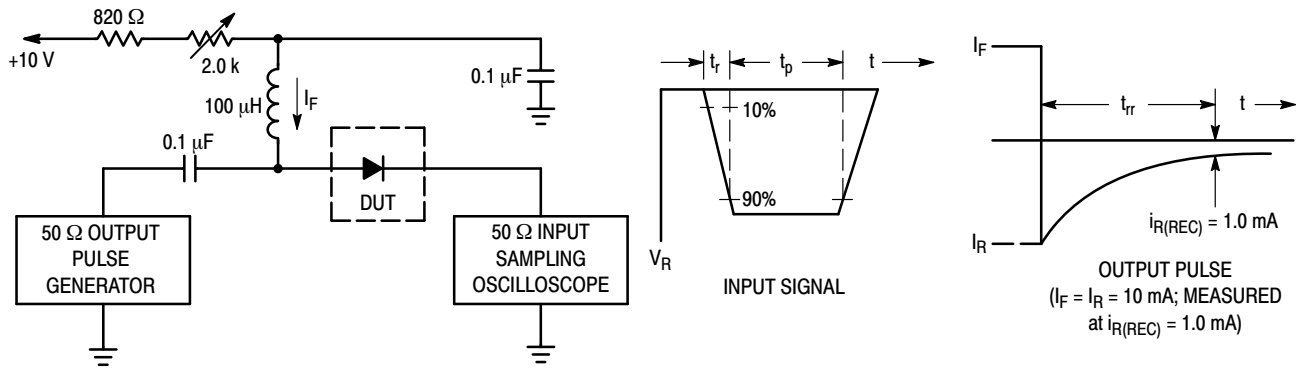
MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_R = 100 \mu\text{A dc}$) MMBD2835LT1G, SMMBD2835LT1G MMBD2836LT1G	$V_{(BR)}$	35 75	- -	Vdc
Reverse Voltage Leakage Current (Note 3) ($V_R = 30 \text{ Vdc}$) MMBD2835LT1G, SMMBD2835LT1G ($V_R = 50 \text{ Vdc}$) MMBD2836LT1G	I_R	- -	100 100	nA dc
Diode Capacitance ($V_R = 0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_T	-	4.0	pF
Forward Voltage ($I_F = 10 \text{ mA dc}$) ($I_F = 50 \text{ mA dc}$) ($I_F = 100 \text{ mA dc}$)	V_F	- - -	1.0 1.0 1.2	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA dc}$, $I_{R(REC)} = 1.0 \text{ mA dc}$) (Figure 1)	t_{rr}	-	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. For each individual diode while the second diode is unbiased.



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

CURVES APPLICABLE TO EACH CATHODE

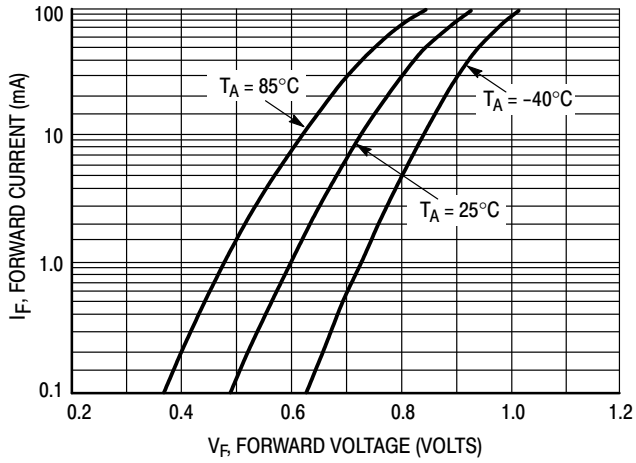


Figure 2. Forward Voltage

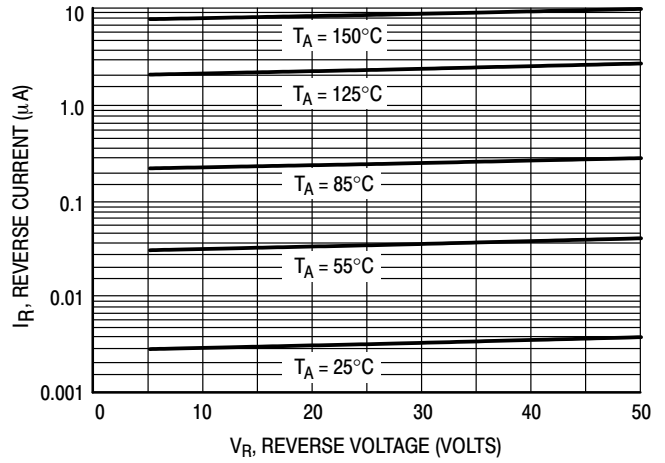


Figure 3. Leakage Current

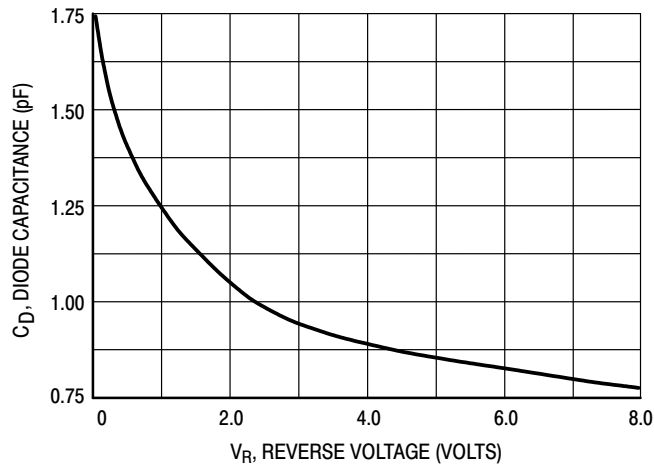
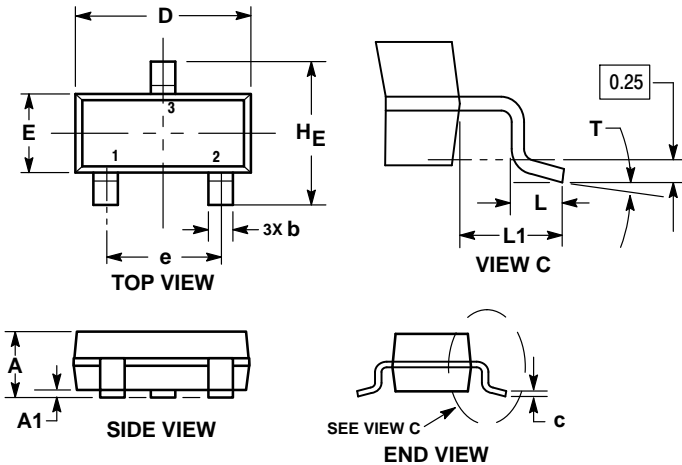


Figure 4. Capacitance

MMBD2835LT1G, MMBD2836LT1G, SMMBD2835LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR



NOTES:

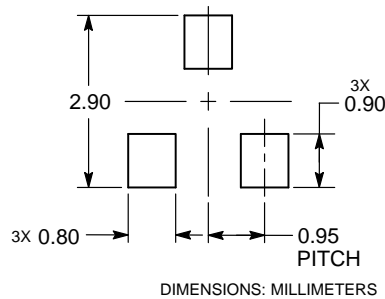
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 12:

1. CATHODE
2. CATHODE
3. ANODE

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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